

Title (en)
Semiconductor packaging method

Title (de)
Halbleitergehäusungsmethode

Title (fr)
Méthode d'encapsulation de semi-conducteur

Publication
EP 2526565 B1 20190220 (EN)

Application
EP 10844172 A 20101207

Priority

- US 73023010 A 20100324
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Abstract (en)
[origin: US2011175217A1] The present technology is directed toward semiconductors packaged by electrically coupling a plurality of die to an upper and lower lead frame. The opposite edges of each corresponding set of leads in the upper lead frame are bent. The leads in the upper lead frame are electrically coupled between respective contacts on respective die and respective lower portion of the leads in the lower lead frame. The bent opposite edges of each corresponding set of leads of the upper lead frame support the upper lead frame before encapsulation, for achieving a desired position of the plurality of die between the leads of the upper and lower lead frames in the packaged semiconductor. After the encapsulated die are separated, the upper leads have an L-shape and electrically couple die contacts on upper side of the die to leads on the lower side of the die so that the package contacts are on the same side of the semiconductor package.

IPC 8 full level
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CPC (source: EP KR US)

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DOCDB simple family (publication)

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